FDP085N10A_F102

N-Channel PowerTrench® MOSFET

100V, 96A, 8.5mΩ

Features

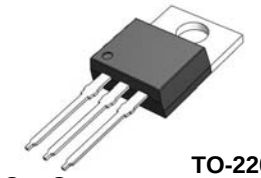
- $R_{DS(on)}$ = 7.35mΩ (Typ.)@ V_{GS} = 10V, I_D = 96A
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC to DC Converters
- Synchronous Rectification for Telecommunication PSU
- Battery Charger
- AC motor drives and Uninterruptible Power Supplies
- Off-line UPS



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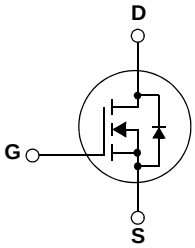

MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DSS}	Drain to Source Voltage			100	V
V_{GSS}	Gate to Source Voltage			±20	V
I_D	Drain Current	-Continuous (T_C = 25°C)		96	A
		-Continuous (T_C = 100°C)		68	
I_{DM}	Drain Current	- Pulsed	(Note 1)	384	A
E_{AS}	Single Pulsed Avalanche Energy		(Note 2)	269	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	6.0	V/ns
P_D	Power Dissipation	(T_C = 25°C)		188	W
		- Derate above 25°C		1.25	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range			-55 to +175	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

Symbol	Parameter	Ratings	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP085N10A	FDP085N10A_F102	TO-220	-	-	50

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V, T_C = 25°C	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, Referenced to 25°C	-	0.07	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 80V, T_C = 150°C	-	-	500	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 96A	-	7.35	8.5	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 96A (Note 4)	-	72	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50V, V_{GS} = 0V f = 1MHz	-	2025	2695	pF
C_{oss}	Output Capacitance		-	468	620	pF
C_{rss}	Reverse Transfer Capacitance		-	20	-	pF
C_{oss}(er)	Engry Releted Output Capacitance	V_{DS} = 50V, V_{GS} = 0V	-	752	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{GS} = 10V, V_{DS} = 50V I_D = 96A (Note 4, 5)	-	31	40	nC
Q_{gs}	Gate to Source Gate Charge		-	9.7	-	nC
Q_{gs2}	Gate Charge Threshoid to Plateau		-	5.0	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	7.5	-	nC
ESR	Equivalent Series Resistance (G-S)	Drain Open, f = 1MHz	-	0.97	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_D = 96A V_{GS} = 10V, R_{GEN} = 4.7Ω (Note 4, 5)	-	18	46	ns
t_r	Turn-On Rise Time		-	22	54	ns
$t_{d(off)}$	Turn-Off Delay Time		-	29	68	ns
t_f	Turn-Off Fall Time		-	8	26	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	96	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	384	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD} = 96A	-	-	1.3	V
t_{rr}	Reverse Recovery Time	V_{DD} = 50V, V_{GS} = 0V, I_{SD} = 96A dI_F/dt = 100A/μs (Note 4)	-	59	-	ns
Q_{rr}	Reverse Recovery Charge		-	80	-	nC

Notes:
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 3 mH, I_{AS} = 13.4 A, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 96 A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test: Pulse width ≤ 300μs, Dual Cycle ≤ 2%
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

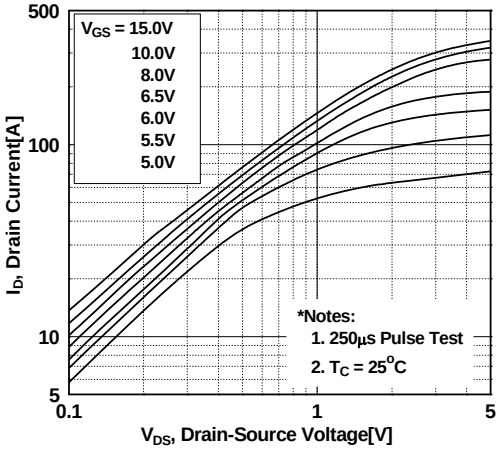

Figure 2. Transfer Characteristics

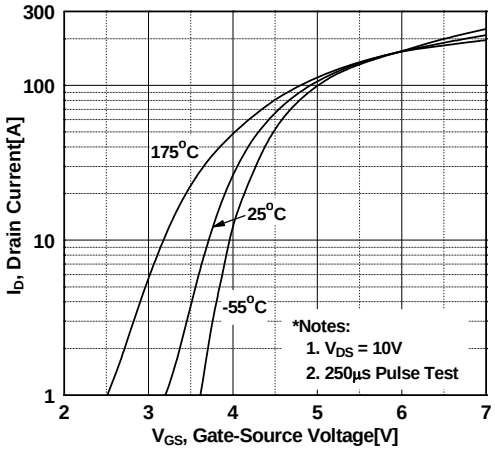

Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

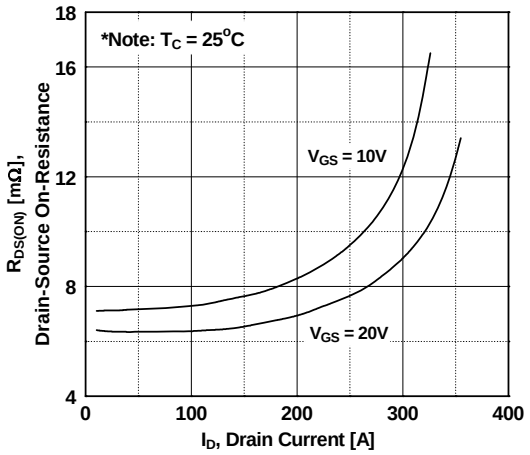

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

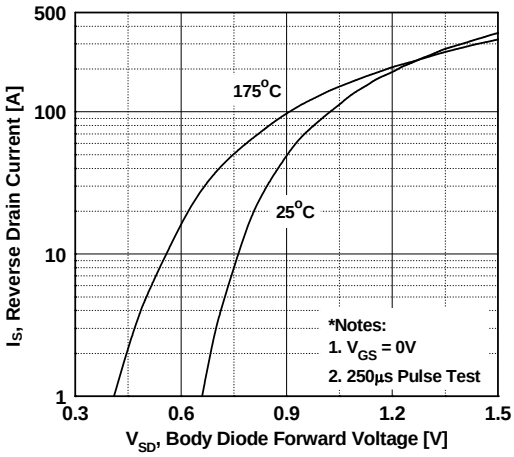

Figure 5. Capacitance Characteristics

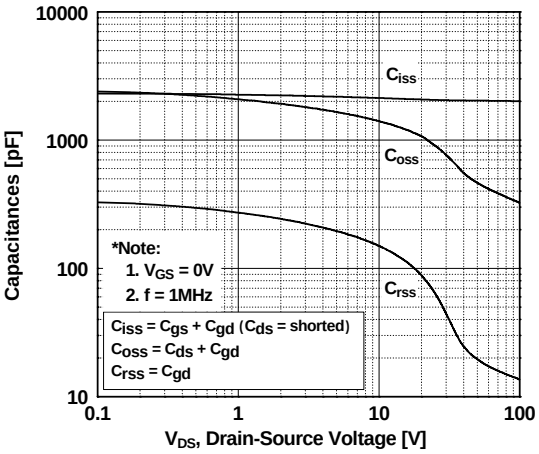

Figure 6. Gate Charge Characteristics